

Model Comparison

Model	VRRMVDRM(V)	ITAVIFAV(A)
C3PDB36N08	800	35
C3PDB36N12	1200	35
C3PDB36N14	1400	35
C3PDB36N16	1600	35
C3PDB36N18	1800	35

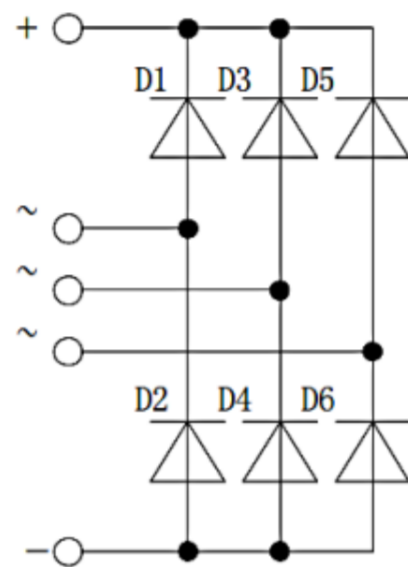
Features / Advantages

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

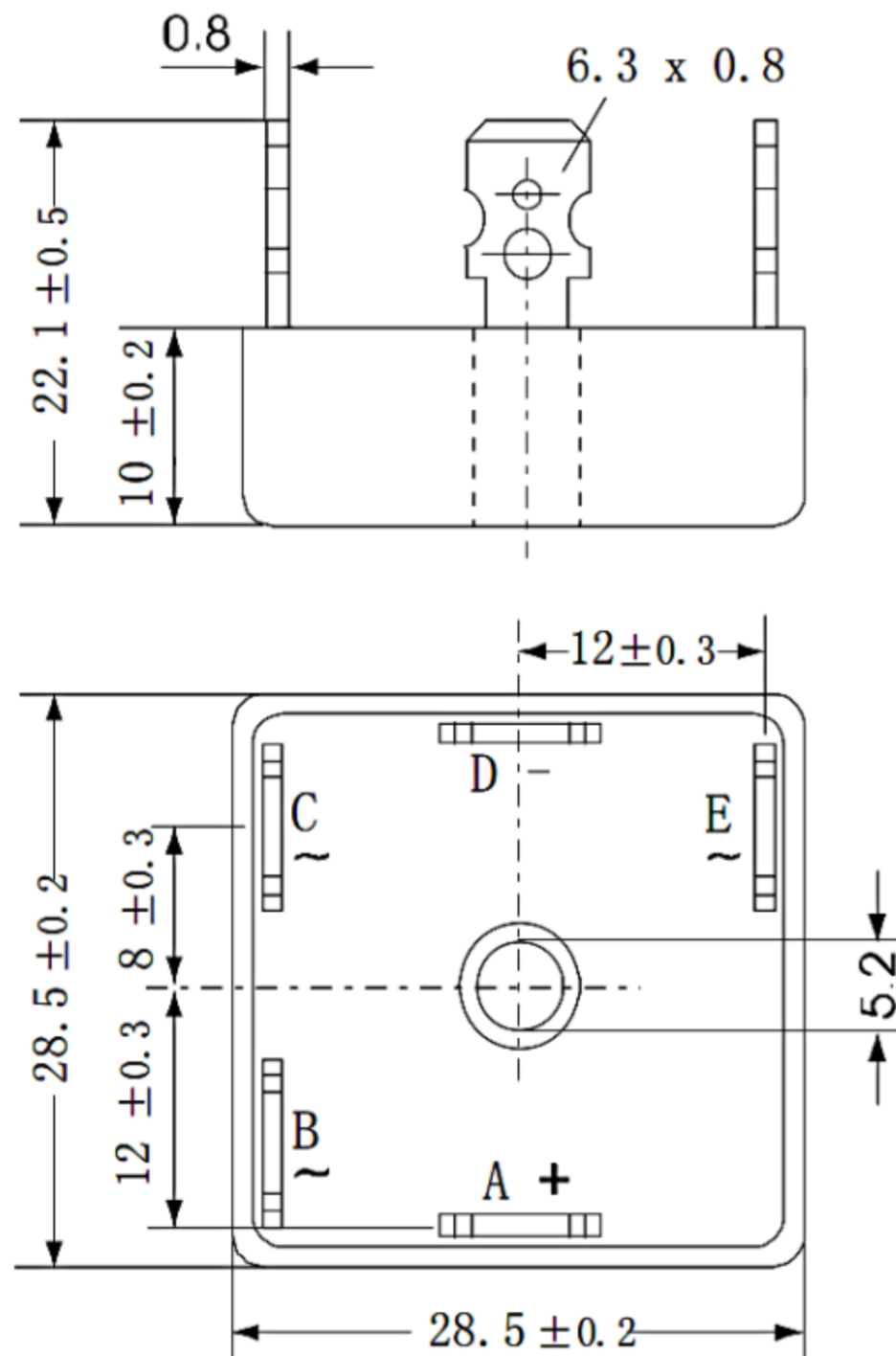
Applications

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Internal Circuit



Package Dimension Dimensions in Millimeters



Parameters

Parametrics	C3PDB36N08~18
V_{DRM} V_{RRM}	800~1800V
I_{dAV} @TC	35A
T_C	85°C
I_{FSM} 10ms, 45°C	450A
$V_{(FO)}$ @ T_{vj} max	0.76V
Package style Outline drawings	MT